

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
12 September 2008 (12.09.2008)

PCT

(10) International Publication Number
WO 2008/107751 A1

(51) International Patent Classification:
H01L 21/762 (2006.01)

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(21) International Application Number:
PCT/IB2008/000383

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(22) International Filing Date:
12 February 2008 (12.02.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0753655 6 March 2007 (06.03.2007) FR

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(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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(54) Title: PROCESS FOR FABRICATING A SUBSTRATE COMPRISING A DEPOSITED BURIED OXIDE LAYER

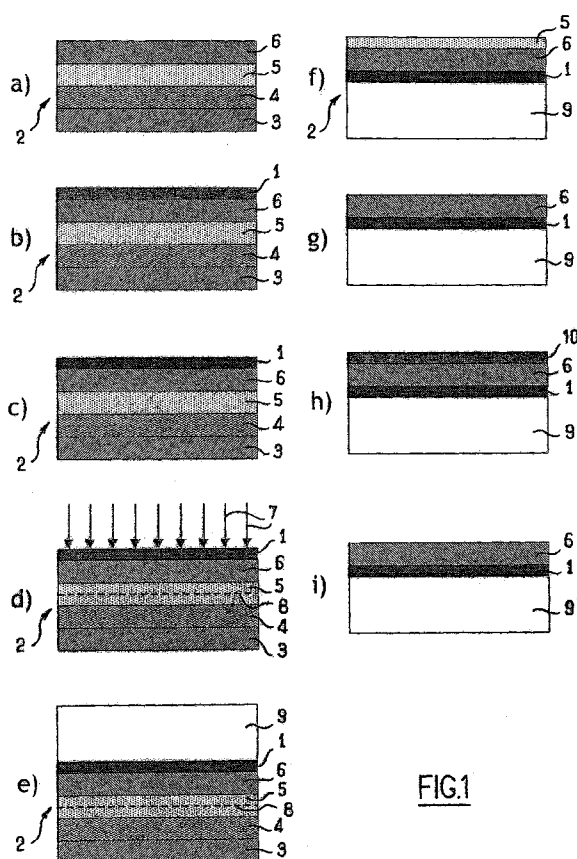


FIG.1

(57) Abstract: Process for fabricating a substrate comprising a buried oxide layer (1) for the production of electronic components or the like, which includes at least one step of depositing an oxide layer (1) or nitride layer on what is called a donor substrate (2) and/or a receiver substrate, and a step of bringing the donor substrate into contact with the receiver substrate (9); said process including at least a first heat treatment of the oxide layer (1) or nitride layer deposited on the donor substrate (2) and/or the receiver substrate, before bonding the donor substrate (2) to the receiver substrate (9), and a second heat treatment of the substrate consisting of the receiver substrate (9), the oxide layer (1) and all or part of the donor substrate (2), at a temperature equal to or higher than the temperature applied in the first heat treatment. Substrate comprising at least an oxide or nitride layer (1) deposited on a donor substrate (2) and/or receiver substrate (9); the oxide or nitride layer (1) being degassed and having a refractive index smaller than the refractive index of an oxide or nitride layer of the same composition formed by thermal growth.

WO 2008/107751 A1



Declaration under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*

Published:

— *with international search report*